



## Description:

The 2N3637 PNP silicon epitaxial planer transistors in a TO-39 type package designed for use as drivers for high power transistors in general purpose amplifier and switching circuits.

## Absolute Maximum Ratings:

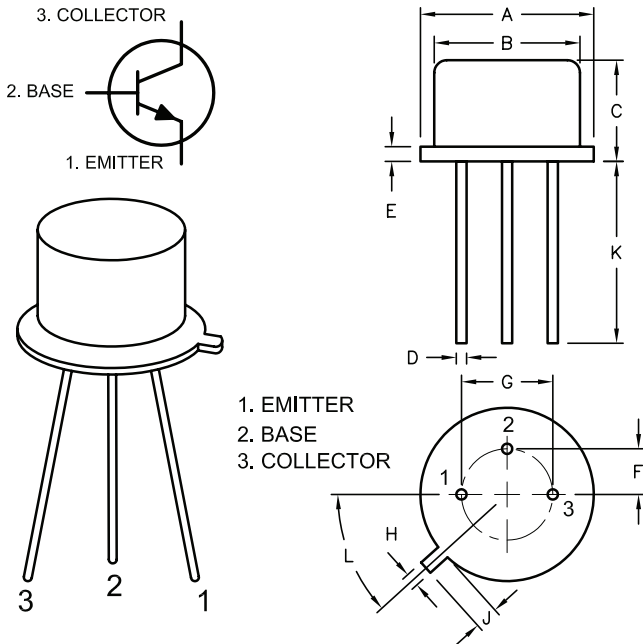
Collector-Emitter Voltage, $V_{CE0}$	: 175V
Collector-Base Voltage ( $I_E = 0$ ), $V_{CBO}$	: 175V
Emitter-Base Voltage ( $I_C = 0$ ), $V_{EBO}$	: 5V
Collector Current, $I_C$	: 1A
Total Device Dissipation ( $T_C = +25^\circ\text{C}$ ), $P_{tot}$	: 5W
Total Device Dissipation ( $T_A = +25^\circ\text{C}$ ), $P_{tot}$	: 1W
Operating Junction Temperature, $T_J$	: $+200^\circ\text{C}$
Storage Temperature Range, $T_{stg}$	: $-65^\circ\text{C}$ to $200^\circ\text{C}$
Thermal Resistance, Junction -to-Case, $R_{thJC}$	: $35^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient, $R_{thJA}$	: $175^\circ\text{C/W}$

## Electrical Characteristics: ( $T_C = +25^\circ\text{C}$ Unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Max	Unit
Collector-Cut-Off Current	$I_{CBO}$	$V_{CE} = 100V, I_E = 0$	-	0.1	$\mu\text{A}$
Emitter Cut-Off Current	$I_{EBO}$	$V_{EB} = 3V, I_C = 0$	-	0.05	$\mu\text{A}$
Collector-Emitter Sustaining Voltage	$V_{CE0(sus)}$	$I_C = 10\text{mA}, I_B = 0, \text{Note 1}$	175	-	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10\text{mA}, I_B = 1\text{mA}, \text{Note 1}$	-	0.3	V
		$I_C = 50\text{mA}, I_B = 5\text{mA}, \text{Note 1}$	-	0.5	V
Base-Emitter Voltage	$V_{BE(sat)}$	$V_{CE} = 5V, I_C = 50\text{mA}$	0.65	0.9	V
DC Current Gain	$h_{FE}$	$I_C = 150\text{mA}, V_{CE} = 10V, \text{Note 1}$	50	-	
		$I_C = 50\text{mA}, V_{CE} = 10V, \text{Note 1}$	100	300	
Transistor Frequency	$f_T$	$V_{CE} = 30V, I_C = 30\text{mA}, f = 100\text{MHz}$	200	-	MHz
Collector Base Capacitance	$C_{cbo}$	$V_{CB} = 20V, I_E = 0, f = 1\text{MHz}$	-	10	pF
Small-Signal Current Gain	$h_{fe}$	$V_{CE} = 10V, I_C = 10\text{mA}, f = 1\text{kHz}$	80	320	

Note 1. Pulse Duration =  $300\mu\text{s}$ , Duty Cycle  $\leq 2\%$

## PNP



Dimensions	A	B	C	D	E	F	G	H	J	K	L
Min.	8.5	7.74	6.09	0.4	-	2.41	4.82	0.71	0.73	12.7	45°
Max.	9.39	8.5	6.6	0.53	0.88	2.66	5.33	0.86	1.02	-	48°

Dimensions : Millimetres

### Part Number Table

Description	Part Number
Transistor, Bipolar, Metal, TO-39, PNP	2N3637

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